

High-Speed Photoreceiver with Si PIN Photodiode



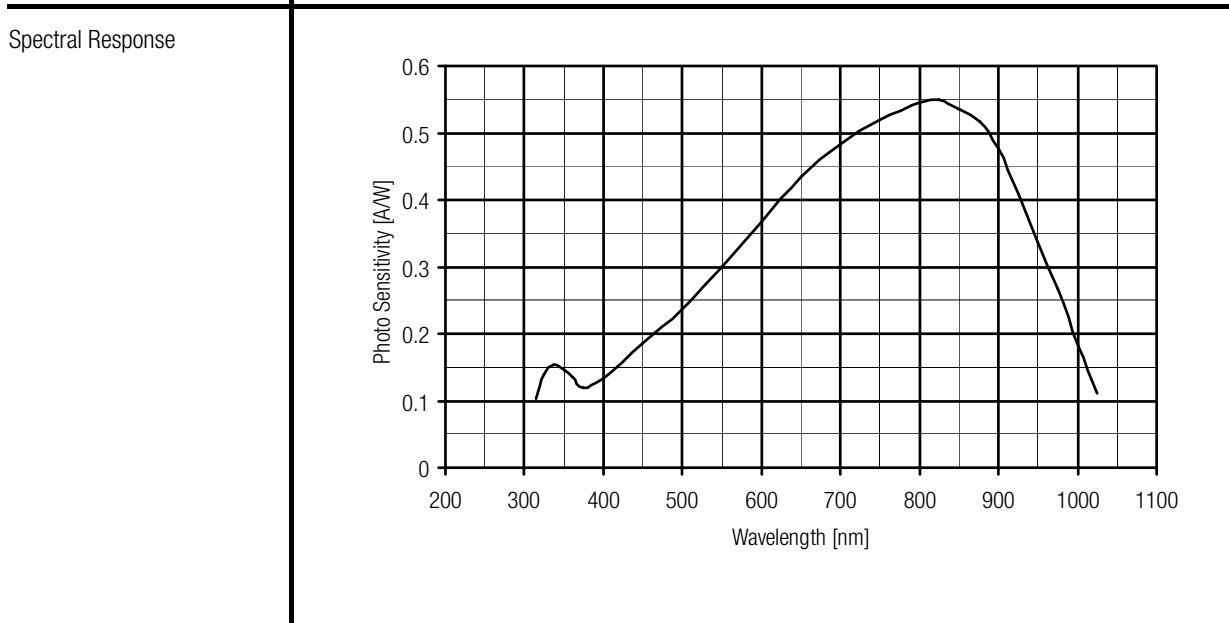
The photoreceiver will be delivered without post holder and post

Features	<ul style="list-style-type: none"> • Si PIN Detector, 0.8 mm Active Diameter • Spectral Range 320 ... 1000 nm • Bandwidth DC ... 200 MHz • Amplifier Transimpedance (Gain) 2.0×10^4 V/A • Max. Conversion Gain 1.1×10^4 V/W (@ 800 nm) 																														
Applications	<ul style="list-style-type: none"> • Spectroscopy • Fast Pulse and Transient Measurements • Optical Triggering • Optical Front-End for Oscilloscopes, A/D Converters and Fast Lock-In Amplifiers 																														
Specifications	<p><i>Test Conditions</i> $V_s = \pm 15$ V, $T_a = 25^\circ$C</p> <table border="0" style="width: 100%;"> <tr> <td style="width: 20%;">Gain</td> <td style="width: 50%;">Transimpedance</td> <td style="width: 30%;">2.0×10^4 V/A (@ 50 Ω load)</td> </tr> <tr> <td></td> <td>Max. Conversion Gain</td> <td>1.1×10^4 V/W (@ 800 nm)</td> </tr> <tr> <td rowspan="4">Frequency Response</td> <td>Lower Cut-Off Frequency</td> <td>DC</td> </tr> <tr> <td>Upper Cut-Off Frequency (-3 dB)</td> <td>200 MHz (± 10 %)</td> </tr> <tr> <td>Rise/Fall Time (10% - 90%)</td> <td>1.8 ns</td> </tr> <tr> <td>Gain Flatness</td> <td>± 1 dB</td> </tr> <tr> <td rowspan="3">Detector</td> <td>Detector Material</td> <td>Si PIN photodiode</td> </tr> <tr> <td>Active Area</td> <td>\varnothing 0.8 mm</td> </tr> <tr> <td>Spectral Response</td> <td>320 ... 1000 nm</td> </tr> <tr> <td rowspan="3">Input</td> <td>Input Offset Compensation</td> <td>± 100 μA adjustable by offset trimpot</td> </tr> <tr> <td>Max. Optical Input Power</td> <td>110 μW (for linear amplification, @ 800 nm)</td> </tr> <tr> <td>Min. NEP</td> <td>9.3 pW/\sqrtHz (@ 800 nm, 10 MHz)</td> </tr> </table>		Gain	Transimpedance	2.0×10^4 V/A (@ 50 Ω load)		Max. Conversion Gain	1.1×10^4 V/W (@ 800 nm)	Frequency Response	Lower Cut-Off Frequency	DC	Upper Cut-Off Frequency (-3 dB)	200 MHz (± 10 %)	Rise/Fall Time (10% - 90%)	1.8 ns	Gain Flatness	± 1 dB	Detector	Detector Material	Si PIN photodiode	Active Area	\varnothing 0.8 mm	Spectral Response	320 ... 1000 nm	Input	Input Offset Compensation	± 100 μ A adjustable by offset trimpot	Max. Optical Input Power	110 μ W (for linear amplification, @ 800 nm)	Min. NEP	9.3 pW/ \sqrt Hz (@ 800 nm, 10 MHz)
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Output	Output Voltage Range $\pm 1.2\text{ V}$ (@ 50 Ω load) for linear operation and low harmonic distortion Max. Output Voltage Range $\pm 1.7\text{ V}$ (@ 50 Ω load) Output Impedance 50 Ω (terminate with 50 Ω load for best performance) Output Noise 18 mV peak-peak (@ 50 Ω load, no signal on photodiode)
Power Supply	Supply Voltage $\pm 15\text{ V}$ Supply Current $\pm 50\text{ mA typ.}$ (depends on operating conditions, recommended power supply capability minimum $\pm 150\text{ mA}$)
Case	Weight 210 g (0.5 lbs) Material AlMg4.5Mn, nickel-plated
Temperature Range	Storage Temperature $-40 \dots +100\text{ }^\circ\text{C}$ Operating Temperature $0 \dots +60\text{ }^\circ\text{C}$

Absolute Maximum Ratings	Optical Input Power 20 mW Power Supply Voltage $\pm 22\text{ V}$
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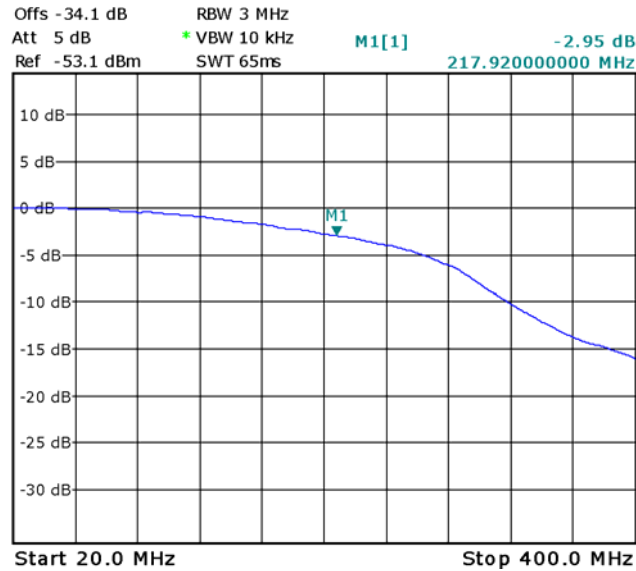


Connectors	Input optical, free space, 25 mm \varnothing round flange compatible with microbench systems Output BNC Power Supply LEMO series 1S, 3-pin fixed socket Pin 1: + 15V Pin 2: - 15V Pin 3: GND
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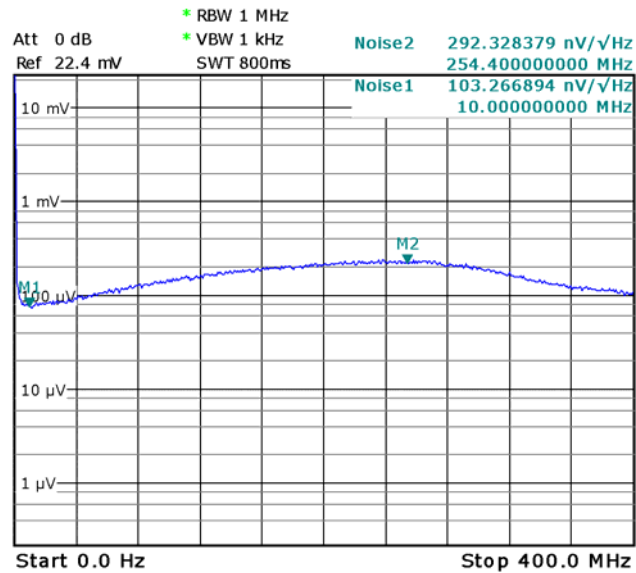
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Typical Performance Characteristics

Frequency Response



Noise Spectrum



Note: Spectral noise data is measured at the amplifier output with darkened photo diode. To determine the spectral input noise divide the measured output noise by the amplifier conversion gain.

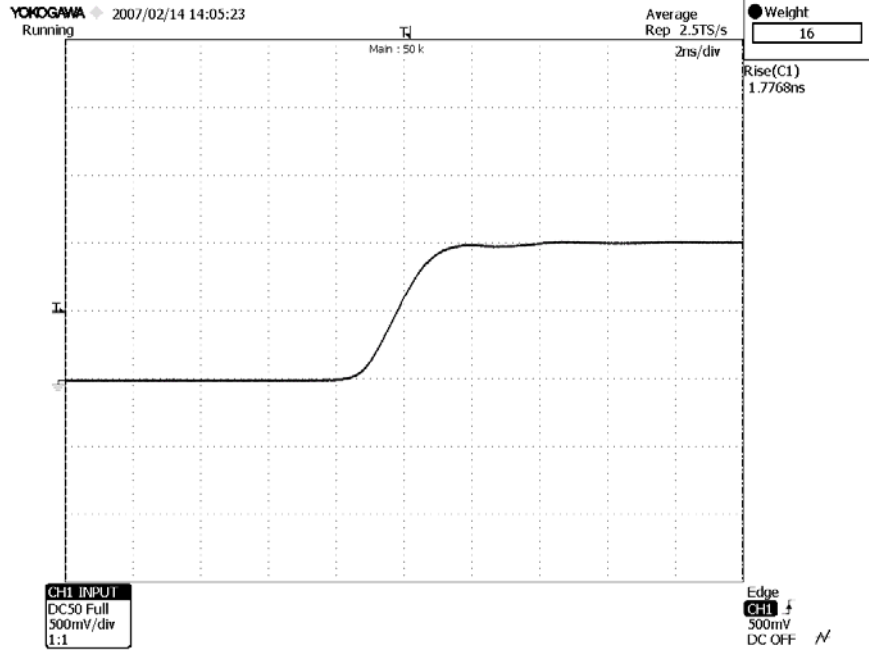
Conversion gain (V/W) = amplifier gain (20,000 V/A) x photo sensitivity (A/W).

Marker	Frequency	Output Noise	Resulting Input Noise (NEP)
1	10 MHz	103 nV/√Hz	9.3 pW/√Hz (@ 800 nm)
2	254 MHz	292 nV/√Hz	27 pW/√Hz (@ 800 nm)

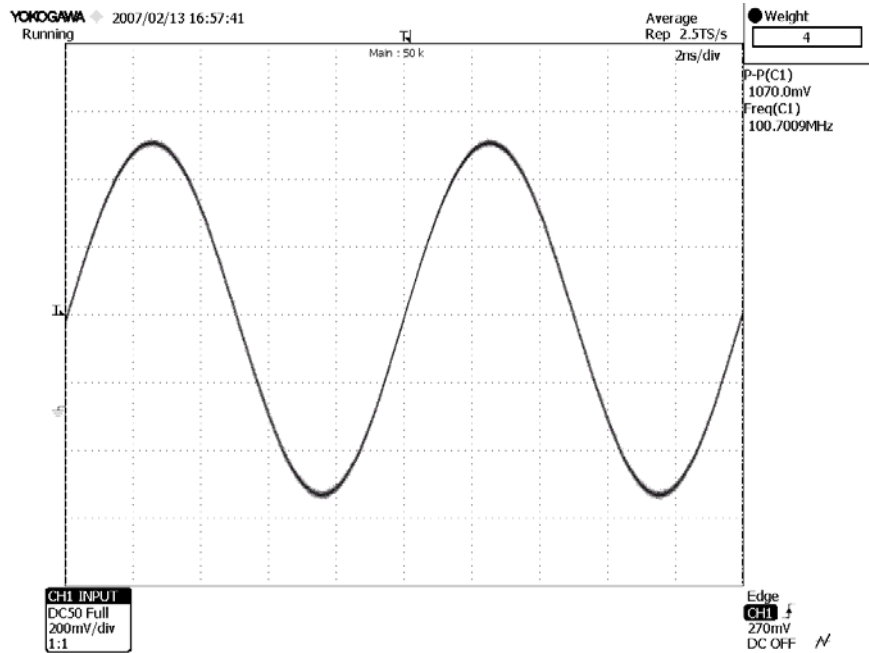
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Typical Performance Characteristics (continued)

Pulse Response to Square Wave Input Signal (with 16 times averaging)



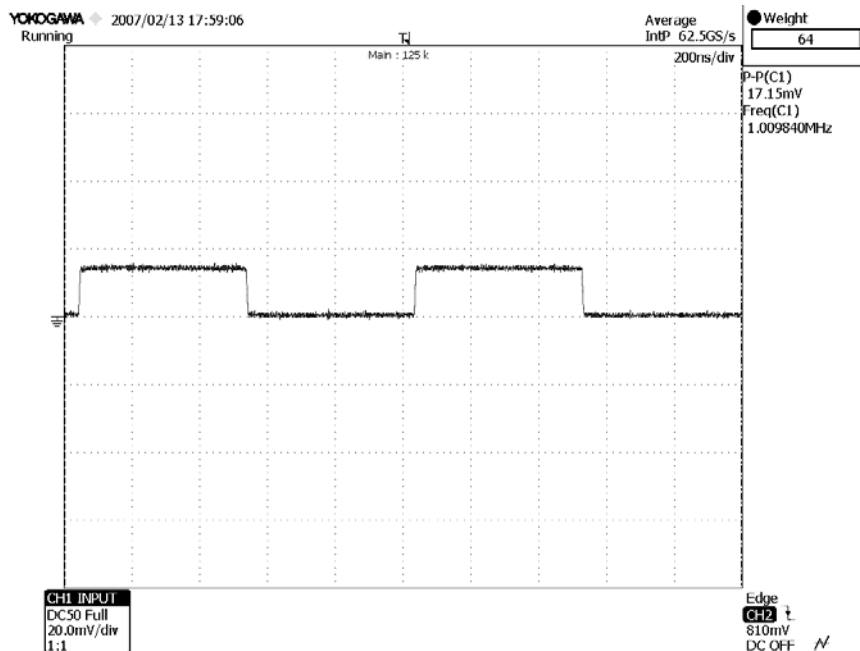
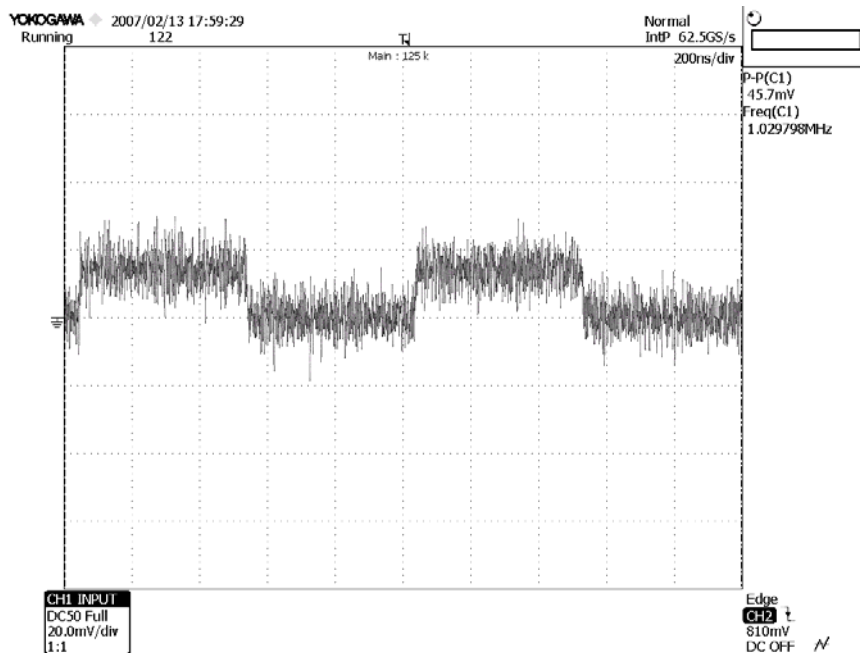
Large Signal Response
output signal for 100 MHz, 100 μ W modulated optical input signal (with 4 times averaging)



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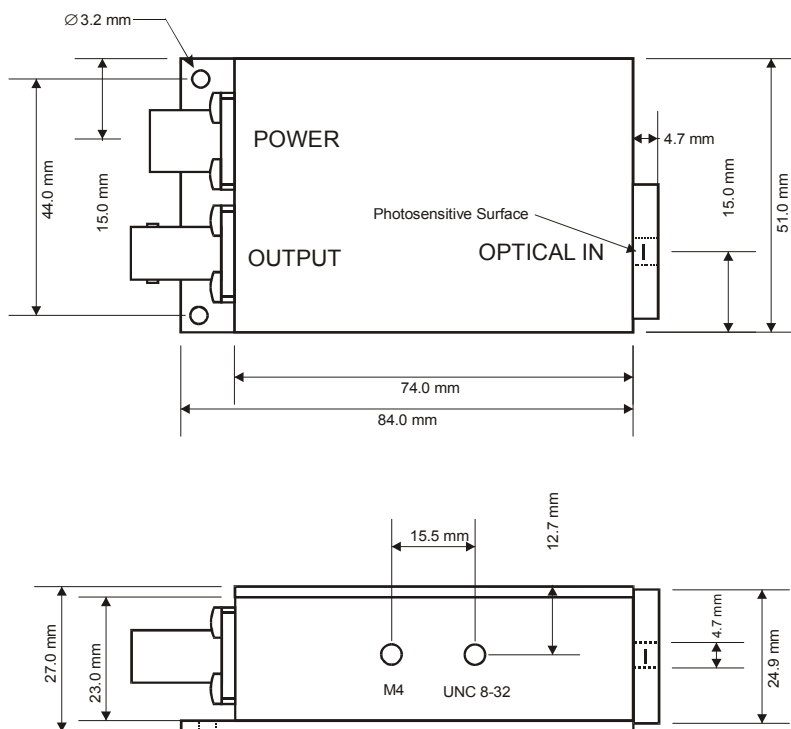
Typical Performance Characteristics (continued)

Small Signal Response
output signal for 1.5 μ W modulated optical input signal, 1 MHz square wave (without (top) and with 64 times averaging (bottom))



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Dimensions



DZ-FWPR_1.cdr

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